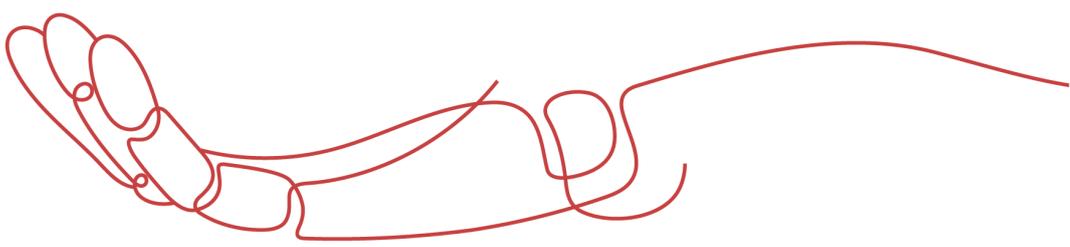


## PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at



**Datasheet**



**Resources**

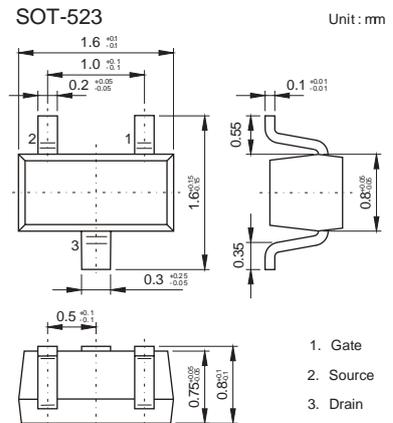
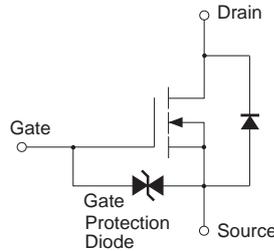


**Samples**

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.jg-semi.cn](http://www.jg-semi.cn). Please email any questions regarding the system integration to [JINGAO\\_questions@jgsemi.com](mailto:JINGAO_questions@jgsemi.com).

### ■ Features

- Low on-resistance.
- Fast switching speed.
- Low voltage drive (2.5V) makes this device ideal for portable equipment.
- Easily designed drive circuits.
- Easy to parallel.



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	
Continuous Drain Current	I <sub>D</sub>	±100	mA
Continuous Drain Current Pulsed *1	I <sub>DP</sub>	±400	
Power Dissipation *2	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

\*1 P<sub>w</sub> ≤ 10μs, Duty cycle ≤ 1%

\*2 With each pin mounted on the recommended lands.

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>BSS</sub>	I <sub>D</sub> =100μA, V <sub>GS</sub> =0V	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =100μA	0.8		1.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4V, I <sub>D</sub> =10mA		5	8	Ω
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1mA		7	13	
Forward Transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =3V, I <sub>D</sub> =10mA	20			mS
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =5V, f=1MHz		13		pF
Output Capacitance	C <sub>oss</sub>			9		
Reverse Transfer Capacitance	C <sub>rss</sub>			4		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =5V, V <sub>DS</sub> =5V, R <sub>L</sub> =500Ω, R <sub>GEN</sub> =10Ω  I <sub>D</sub> =10mA		15		ns
Turn-On Rise Time	t <sub>r</sub>			35		
Turn-Off DelayTime	t <sub>d(off)</sub>			80		
Turn-Off Fall Time	t <sub>f</sub>			80		

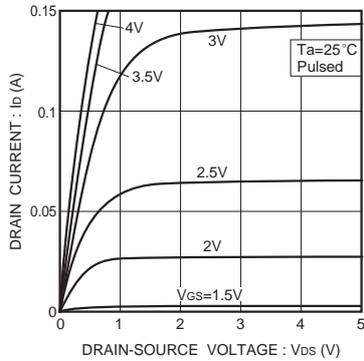
**■ Typical Characteristics**


Fig.1 Typical output characteristics

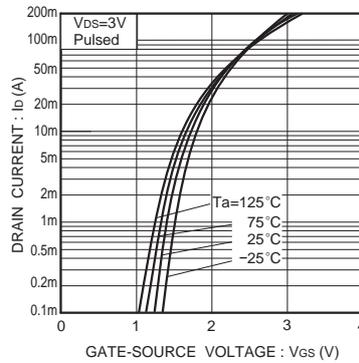


Fig.2 Typical transfer characteristics

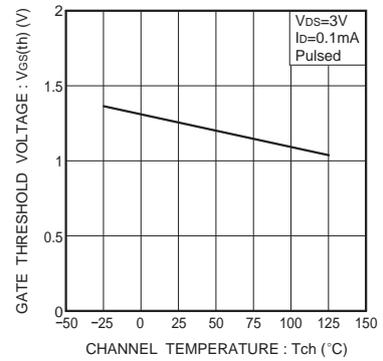


Fig.3 Gate threshold voltage vs. channel temperature

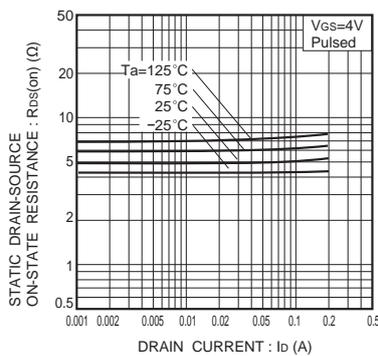


Fig.4 Static drain-source on-state resistance vs. drain current ( I )

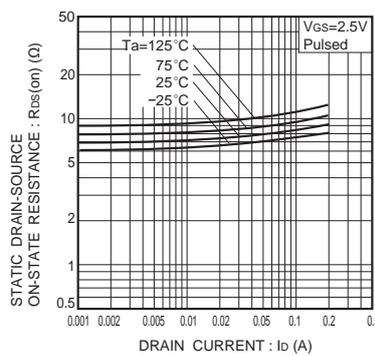


Fig.5 Static drain-source on-state resistance vs. drain current (II)

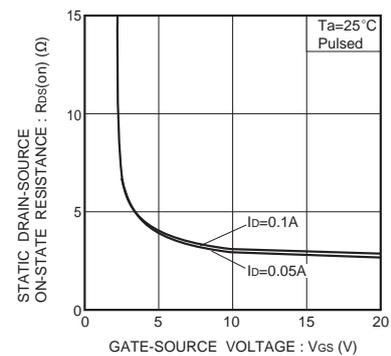


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

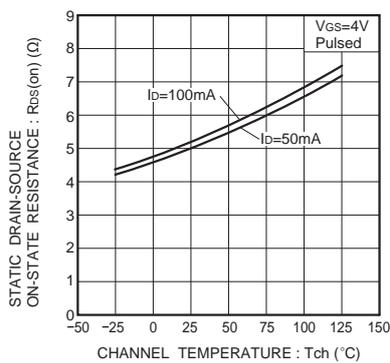


Fig.7 Static drain-source on-state resistance vs. channel temperature

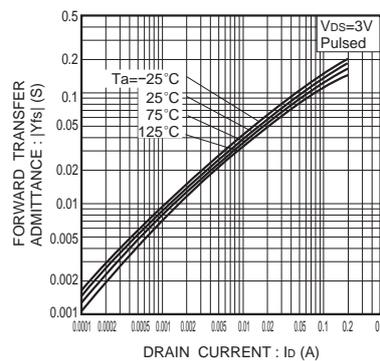


Fig.8 Forward transfer admittance vs. drain current

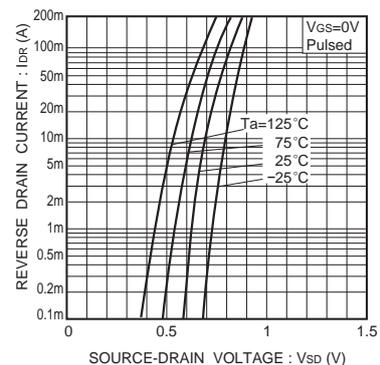


Fig.9 Reverse drain current vs. source-drain voltage ( I )

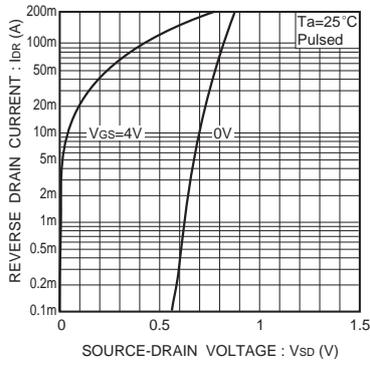
**■ Typical Characteristics**


Fig.10 Reverse drain current vs. source-drain voltage (II)

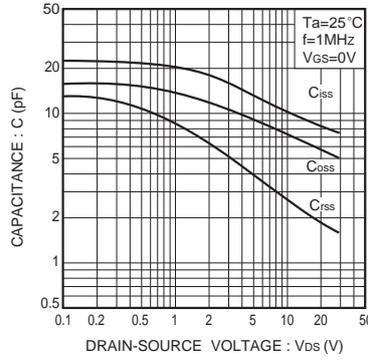


Fig.11 Typical capacitance vs. drain-source voltage

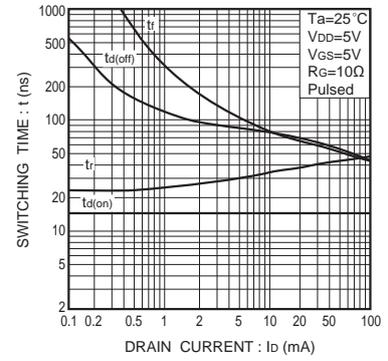


Fig.12 Switching characteristics

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